



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

TO-92 Plastic-Encapsulate Transistors

C1815 TRANSISTOR (NPN)

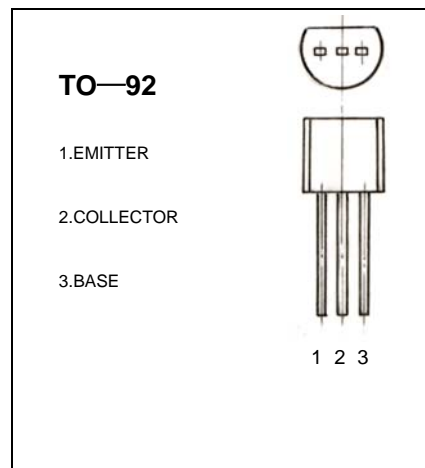
FEATURES

Power dissipation

MAXIMUM RATINGS* $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	150	mA
P_D	Total Device Dissipation	200	mW
T_J, T_{stg}	Junction and Storage Temperature	-55-150	$^{\circ}\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C=100\text{ }\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C=0.1\text{ mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E=100\text{ }\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{ V}, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=50\text{ V}, I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{ V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6\text{ V}, I_C=2\text{ mA}$	70		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{ mA}, I_B=10\text{ mA}$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{ mA}, I_B=10\text{ mA}$			1	V
Transition frequency	f_T	$V_{CE}=10\text{ V}, I_C=1\text{ mA}, f=30\text{ MHz}$	80			MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10\text{ V}, I_E=0, f=1\text{ MHz}$			3.5	pF
Noise Figure	NF	$V_{CE}=6\text{ V}, I_C=0.1\text{ mA}, f=1\text{ KHz}, R_G=10\text{ K}$			10	dB

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR	BL
Range	70-140	120-240	200-400	350-700

Typical Characteristics

C1815

